

“HALF-BRIDGE” IGBT

Feature

- IGBT New Technology
- Low $V_{CE(sat)}$
- Low Turn-off losses
- Short tail current
- Positive temperature coefficient

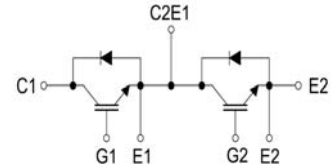
Application

- AC & DC Motor controls
- General purpose inverters
- Optimized for high current inverter
- Servo Controls
- UPS, Robotics



Package : V1

$V_{CES} = 600V$
 $I_c = 150A$
 $V_{CE(ON)} \text{ typ.} = 1.5V$
@ $I_c = 150A$



Absolute Maximum Ratings @ $T_j = 25^\circ C$ (Per Leg)

Symbol	Parameter	Condition	Ratings	Unit
V_{CES}	Collector-to-Emitter Voltage	$T_c = 25^\circ C$	600	V
V_{GES}	Gate emitter voltage		± 20	V
I_c	Continuous Collector Current	$T_c = 80^\circ C (25^\circ C)$	150 (210)	A
I_{CP}	Pulsed collector current	$T_c = 25^\circ C$	300	A
I_F	Diode Continuous Forward Current	$T_c = 80^\circ C (25^\circ C)$	150 (210)	A
I_{FM}	Diode Maximum Forward Current	$T_c = 25^\circ C$	300	A
t_p	Short circuit test, $V_{GE} = 15V, V_{CC} = 360V$	$T_c = 150^\circ C (25^\circ C)$	6 (8)	μs
V_{iso}	Isolation Voltage test	AC @ 1 minute	2500	V
T_j	Junction Temperature		-40 ~ 150	$^\circ C$
T_{stg}	Storage Temperature		-40 ~ 125	$^\circ C$
Weight	Weight of Module		190	g
Md	Mounting torque with screw : M5		2.0	N.m
	Terminal connection torque : M5		2.0	N.m

Static Characteristics @ $T_j = 25^\circ C$ (unless otherwise specified)

Parameters		Min	Typ	Max	Unit	Test conditions
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	1.05	1.50	1.95	V	$I_c = 150A, V_{GE} = 15V$
$V_{GE(th)}$	Gate Threshold Voltage	5.0	5.8	6.5		$V_{CE} = V_{GE}, I_c = 4mA$
I_{CES}	Zero Gate Voltage Collector Current	—	—	5.0	mA	$V_{GE} = 0V, V_{CE} = 600V$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	400	nA	$V_{CE} = 0V, V_{GE} = 20V$
V_F	Forward voltage drop	1.2	1.6	1.9	V	$I_F = 150A$
R_{GINT}	Integrated gate resistor	—	2	—	Ω	

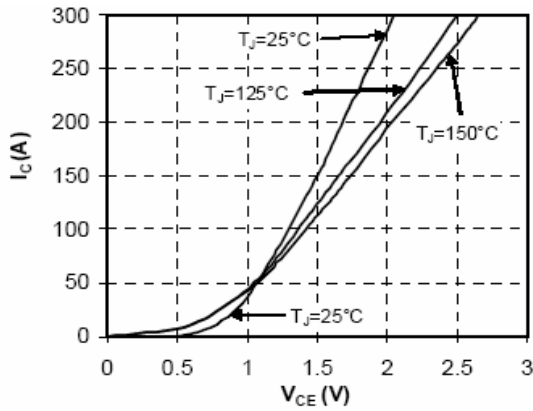
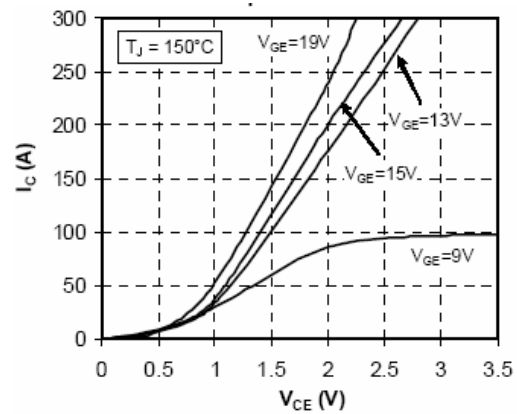
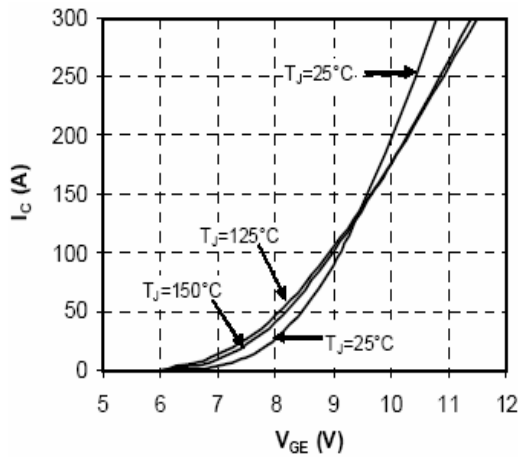
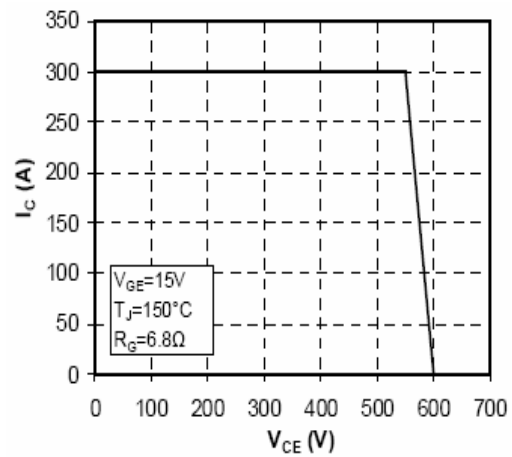
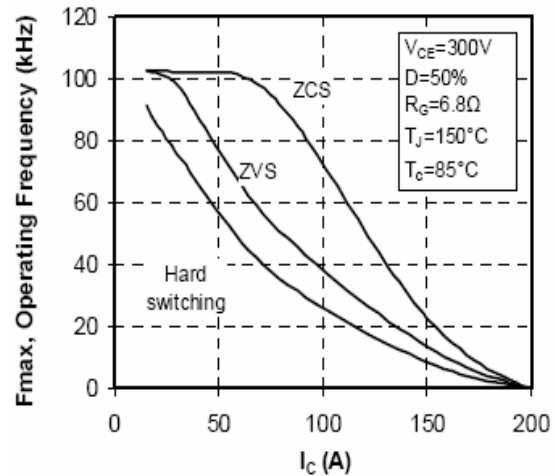
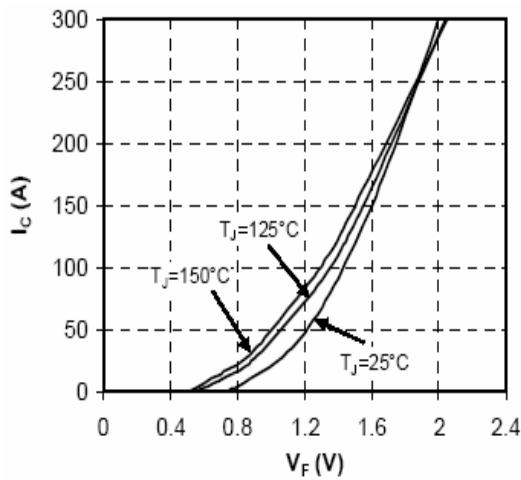
Electrical Characteristic Values (IGBT / DIODE) @ T_j = 25°C (unless otherwise specified)

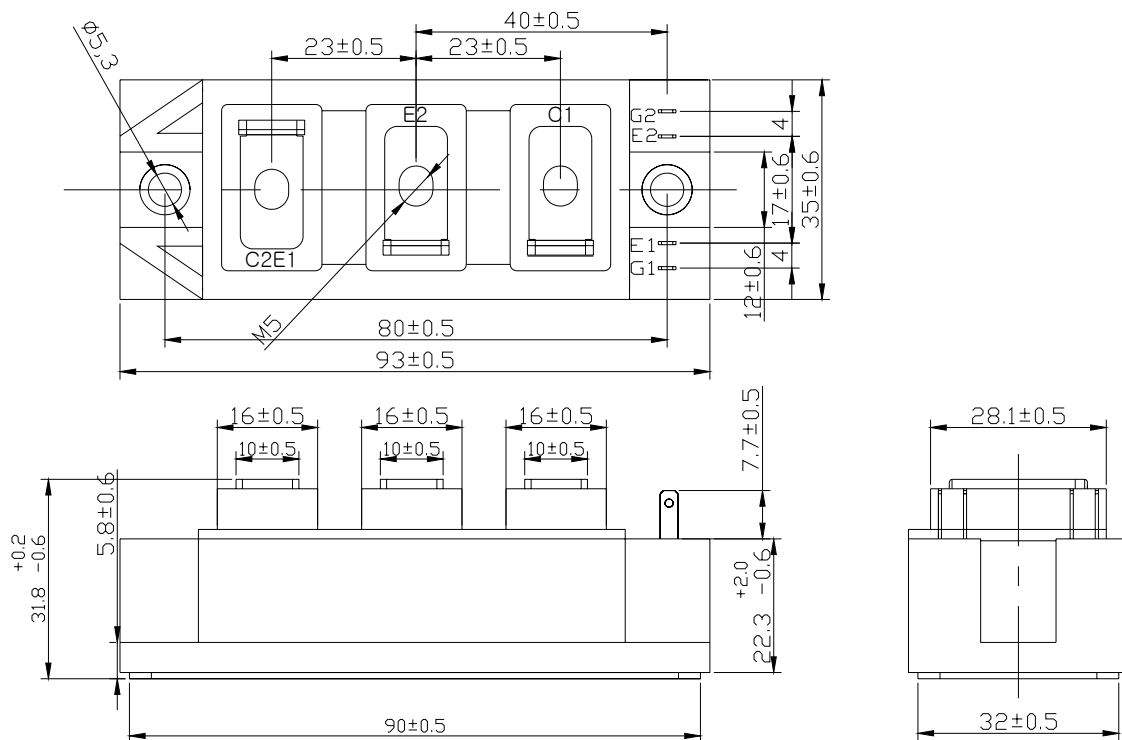
Parameters		Min	Typ	Max	Unit	Test conditions
C _{iss}	Input capacitance	—	9200	—	pF	V _{CE} = 25V, V _{GE} = 0V f = 1 MHz
C _{oss}	Output capacitance	—	580	—		
C _{rss}	Reverse transfer capacitance	—	270	—		
t _{d(on)}	Turn-on delay time	—	125	—	ns	Inductive Switching (125°C) V _{CC} = 300V I _C = 150A, V _{GE} = ±15V R _G = 3.3Ω
t _r	Rise time	—	30	—		
t _{d(off)}	Turn-off delay time	—	340	—		
t _f	Fall time	—	60	—		
V _{BR}	Cathode-Anode breakdown Voltage	600	—	—	V	
I _{RM}	Maximum Reverse Leakage Current	—	—	250	μA	V _R = 600V
t _{rr}	Reverse Recovery Time	—	130	—	ns	I _F = 150A, V _R = 300V
Q _{rr}	Reverse Recovery Charge	—	6.9	—	μC	di / dt = 2100A / μs

Thermal Characteristics

Symbol	Parameter	Min	Typ	Max	Unit
R _{θJC}	Junction-to-Case (IGBT Part, Per 1/2 Module)	-	-	0.44	°C/W
R _{θJC}	Junction-to-Case (Diode Part, Per 1/2 Module)	-	-	0.77	
R _{θCS}	Case-to-Heat Sink (Conductive grease applied)	-	0.05	-	

※ Data and specifications subject to change without notice.


Fig 1. Typ. IGBT Output Characteristics

Fig 2. Typ. IGBT Out Characteristics

Fig 3. Typ. Transfer Characteristics

Fig 4. Reverse Bias Operating Area


Package Outline (dimensions in mm)


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